

74LVC02A

Low-Voltage CMOS Quad 2-Input NOR Gate

With 5 V-Tolerant Inputs

The 74LVC02A is a high performance, quad 2-input NOR gate operating from a 1.2 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows 74LVC02A inputs to be safely driven from 5 V devices.

Current drive capability is 24 mA at the outputs.

Features

- Designed for 1.2 V to 3.6 V V_{CC} Operation
- 5 V Tolerant Inputs – Interface Capability With 5 V TTL Logic
- 24 mA Output Sink and Source Capability
- Near Zero Static Supply Current (10 μ A) Substantially Reduces System Power Requirements
- ESD Performance: Human Body Model >2000 V;
Machine Model >200 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

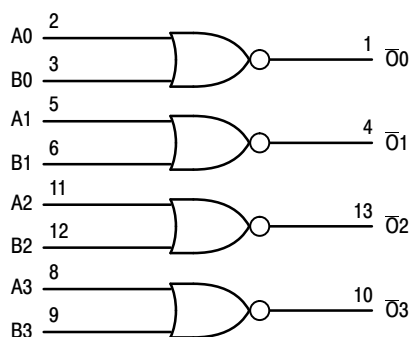


Figure 1. Logic Diagram

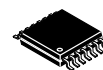


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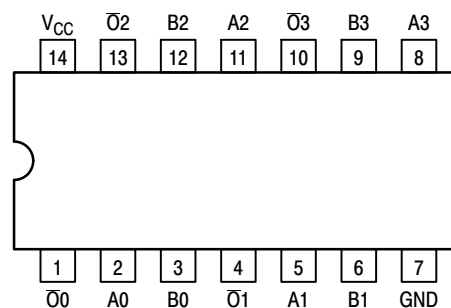


SOIC-14 NB
D SUFFIX
CASE 751A

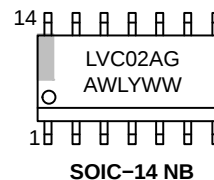


TSSOP-14
DT SUFFIX
CASE 948G

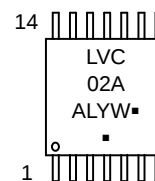
PIN ASSIGNMENT



MARKING DIAGRAMS



SOIC-14 NB



TSSOP-14

A = Assembly Location
WL, L = Wafer Lot
Y = Year
WW, W = Work Week
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

74LVC02A

PIN NAMES

Pins	Function
An, Bn	Data Inputs
$\bar{O}n$	Outputs

TRUTH TABLE

Inputs		Outputs
An	Bn	$\bar{O}n$
L	L	H
L	H	L
H	L	L
H	H	L

H = High Voltage Level

L = Low Voltage Level

For I_{CC} reasons, DO NOT FLOAT Inputs

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MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V_{CC}	DC Supply Voltage	-0.5 to +6.5		V
V_I	DC Input Voltage	$-0.5 \leq V_I \leq +6.5$		V
V_O	DC Output Voltage	$-0.5 \leq V_O \leq V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I_{IK}	DC Input Diode Current	-50	$V_I < GND$	mA
I_{OK}	DC Output Diode Current	-50	$V_O < GND$	mA
		+50	$V_O > V_{CC}$	mA
I_O	DC Output Source/Sink Current	± 50		mA
I_{CC}	DC Supply Current Per Supply Pin	± 100		mA
I_{GND}	DC Ground Current Per Ground Pin	± 100		mA
T_{STG}	Storage Temperature Range	-65 to +150		°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds	$T_L = 260$		°C
T_J	Junction Temperature Under Bias	$T_J = 135$		°C
θ_{JA}	Thermal Resistance (Note 2)	SOIC = 85 TSSOP = 100		°C/W
MSL	Moisture Sensitivity		Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I_O absolute maximum rating must be observed.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Units
V_{CC}	Supply Voltage Operating Functional	1.65 1.2		3.6 3.6	V
V_I	Input Voltage	0		5.5	V
V_O	Output Voltage HIGH or LOW State 3-State	0 0		V_{CC} 5.5	V
I_{OH}	HIGH Level Output Current $V_{CC} = 3.0\text{ V} - 3.6\text{ V}$ $V_{CC} = 2.7\text{ V} - 3.0\text{ V}$			-24 -12	mA
I_{OL}	LOW Level Output Current $V_{CC} = 3.0\text{ V} - 3.6\text{ V}$ $V_{CC} = 2.7\text{ V} - 3.0\text{ V}$			24 12	mA
T_A	Operating Free-Air Temperature	-40		+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate $V_{CC} = 1.65\text{ V to } 2.7\text{ V}$ $V_{CC} = 2.7\text{ V to } 3.6\text{ V}$	0 0		20 10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	-40°C to +85°C			-40°C to +125°C			Unit
			Min	Typ (Note 3)	Max	Min	Typ (Note 3)	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.2 V	1.08	–	–	1.08	–	–	V
		V _{CC} = 1.65 V to 1.95 V	0.65 x V _{CC}	–	–	0.65 x V _{CC}	–	–	
		V _{CC} = 2.3 V to 2.7 V	1.7	–	–	1.7	–	–	
		V _{CC} = 2.7 V to 3.6 V	2.0	–	–	2.0	–	–	
V _{IL}	LOW-level input voltage	V _{CC} = 1.2 V	–	–	0.12	–	–	0.12	V
		V _{CC} = 1.65 V to 1.95 V	–	–	0.35 x V _{CC}	–	–	0.35 x V _{CC}	
		V _{CC} = 2.3 V to 2.7 V	–	–	0.7	–	–	0.7	
		V _{CC} = 2.7 V to 3.6 V	–	–	0.8	–	–	0.8	
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}							V
		I _O = –100 µA; V _{CC} = 1.65 V to 3.6 V	V _{CC} – 0.2	–	–	V _{CC} – 0.3	–	–	
		I _O = –4 mA; V _{CC} = 1.65 V	1.2	–	–	1.05	–	–	
		I _O = –8 mA; V _{CC} = 2.3 V	1.8	–	–	1.65	–	–	
		I _O = –12 mA; V _{CC} = 2.7 V	2.2	–	–	2.05	–	–	
		I _O = –18 mA; V _{CC} = 3.0 V	2.4	–	–	2.25	–	–	
		I _O = –24 mA; V _{CC} = 3.0 V	2.2	–	–	2.0	–	–	
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}							V
		I _O = 100 µA; V _{CC} = 1.65 V to 3.6 V	–	–	0.2	–	–	0.3	
		I _O = 4 mA; V _{CC} = 1.65 V	–	–	0.45	–	–	0.65	
		I _O = 8 mA; V _{CC} = 2.3 V	–	–	0.6	–	–	0.8	
		I _O = 12 mA; V _{CC} = 2.7 V	–	–	0.4	–	–	0.6	
		I _O = –24 mA; V _{CC} = 3.0 V	–	–	0.55	–	–	0.8	
I _I	Input leakage current	V _I = 5.5V or GND V _{CC} = 3.6 V	–	±0.1	±5	–	±0.1	±20	µA
I _{OFF}	Power-off leakage current	V _I or V _O = 5.5 V; V _{CC} = 0.0 V	–	±0.1	±10	–	±0.1	±20	µA
I _{CC}	Supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 3.6 V	–	0.1	10	–	0.1	40	µA
ΔI _{CC}	Additional supply current	per input pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 2.7 V to 3.6 V	–	5	500	–	5	5000	µA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. All typical values are measured at T_A = 25°C and V_{CC} = 3.3 V, unless stated otherwise.

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AC ELECTRICAL CHARACTERISTICS ($t_R = t_F = 2.5 \text{ ns}$)

Symbol	Parameter	Conditions	-40°C to +85°C			-40°C to +125°C			Unit
			Min	Typ ¹	Max	Min	Typ ¹	Max	
t_{pd}	Propagation Delay (Note 5)	$V_{CC} = 1.2 \text{ V}$	–	14.0	–	–	–	–	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.5	4.0	8.6	0.5	–	10.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.5	2.4	4.9	0.5	–	5.7	ns
		$V_{CC} = 2.7 \text{ V}$	0.5	2.5	5.1	0.5	–	6.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.5	2.2	4.4	0.5	–	5.5	ns
$t_{sk(0)}$	Output Skew Time (Note 6)	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	–	–	1.0	–	–	1.5	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Typical values are measured at $T_A = 25^\circ\text{C}$ and $V_{CC} = 3.3 \text{ V}$, unless stated otherwise.

5. t_{pd} is the same as t_{PLH} and t_{PHL} .

6. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Characteristic	Condition	$T_A = +25^\circ\text{C}$			Unit
			Min	Typ	Max	
V_{OLP}	Dynamic LOW Peak Voltage (Note 7)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ $V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		0.8 0.6		V
V_{OLV}	Dynamic LOW Valley Voltage (Note 7)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ $V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		–0.8 –0.6		V

7. Number of outputs defined as “n”. Measured with “n–1” outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	4.0	pF
C_{OUT}	Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	5.0	pF
C_{PD}	Power Dissipation Capacitance (Note 8)	Per input; $V_I = \text{GND or } V_{CC}$		pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.5	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	5.7	
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	8.5	

8. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

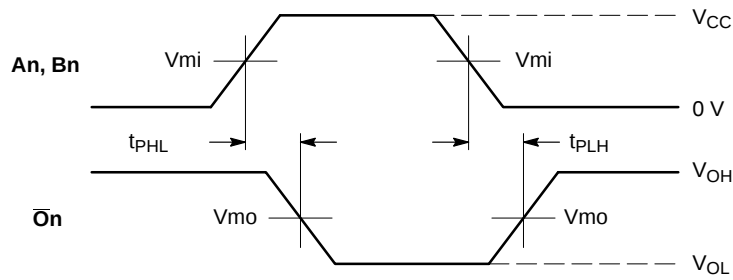
f_i = input frequency in MHz; f_o = output frequency in MHz

C_L = output load capacitance in pF V_{CC} = supply voltage in Volts

N = number of outputs switching

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

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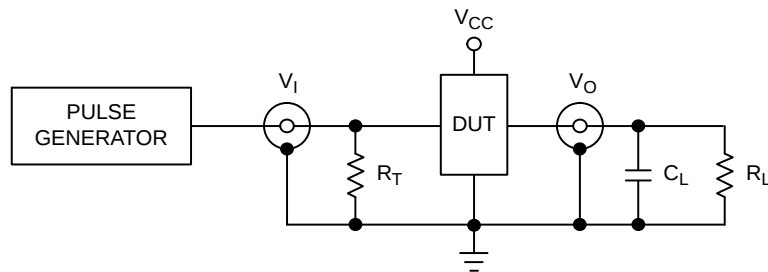


WAVEFORM 1 – PROPAGATION DELAYS

$t_R = t_F = 2.5 \text{ ns}$, 10% to 90%; $f = 1 \text{ MHz}$; $t_W = 500 \text{ ns}$

Symbol	Vcc		
	3.3 V $\pm$ 0.3 V	2.7 V	Vcc < 2.7 V
Vmi	1.5 V	1.5 V	Vcc/2
Vmo	1.5 V	1.5 V	Vcc/2

Figure 2. AC Waveforms



C_L includes jig and probe capacitance
 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Supply Voltage	Input		Load	
Vcc (V)	VI	tr, tf	CL	RL
1.2	Vcc	$\leq 2 \text{ ns}$	30 pF	1 k Ω
1.65 – 1.95	Vcc	$\leq 2 \text{ ns}$	30 pF	1 k Ω
2.3 – 2.7	Vcc	$\leq 2 \text{ ns}$	30 pF	500 Ω
2.7	2.7 V	$\leq 2.5 \text{ ns}$	50 pF	500 Ω
3 – 3.6	2.7 V	$\leq 2.5 \text{ ns}$	50 pF	500 Ω

Figure 3. Test Circuit

ORDERING INFORMATION

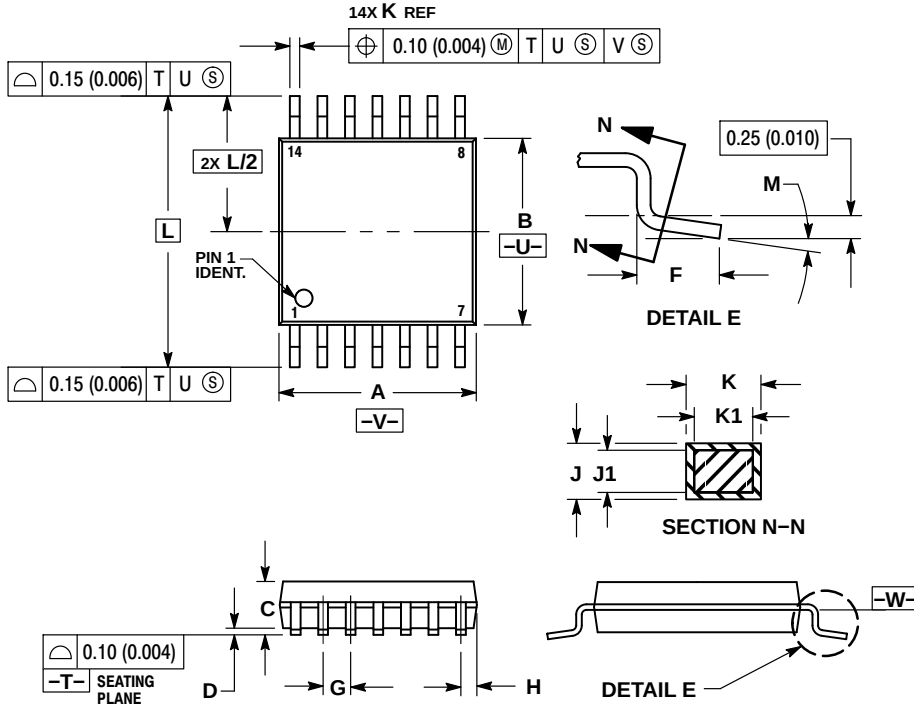
Device	Package	Shipping [†]
74LVC02ADR2G	SOIC-14 NB (Pb-Free)	2500 / Tape & Reel
74LVC02ADTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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PACKAGE DIMENSIONS

TSSOP-14
DT SUFFIX
CASE 948G
ISSUE B

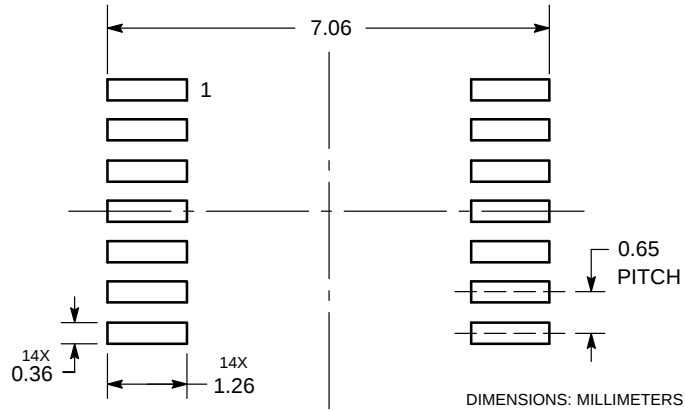


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	—	1.20	—	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC	—	0.026 BSC	—
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC	—	0.252 BSC	—
M	0°	8°	0°	8°

SOLDERING FOOTPRINT*

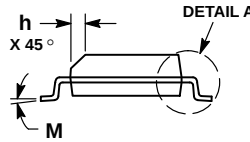
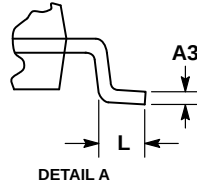
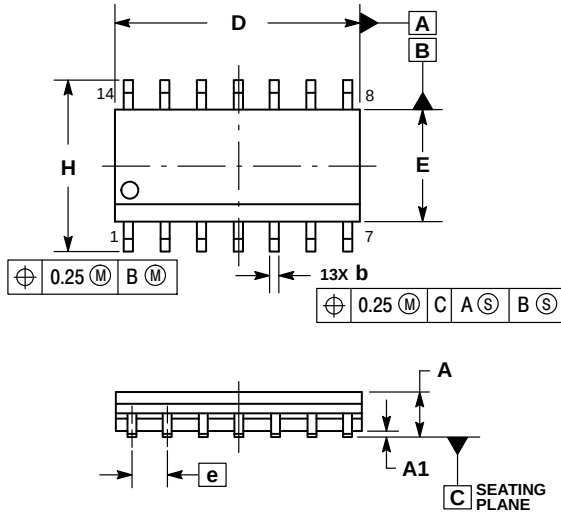


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

SOIC-14 NB CASE 751A-03 ISSUE K

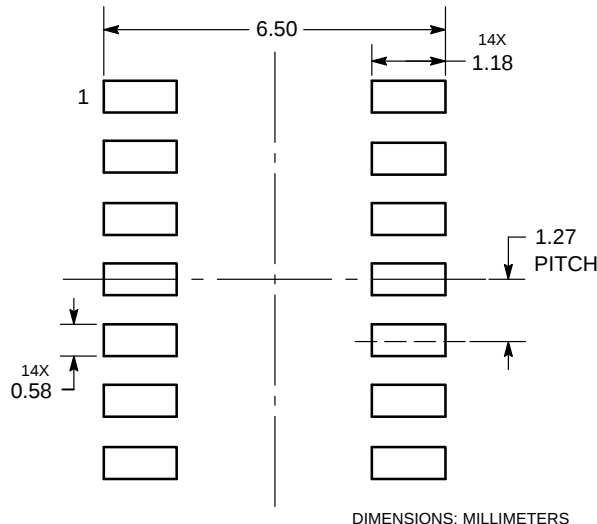


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

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Электрон
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Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

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